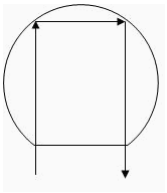
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	<110> +/- 1 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none/semi std	
	5.0	Overall Thickness	675.00 +/- 22.00 µm	ADE 100%
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Bow	<70.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<70.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor - Topsil only
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Thickness	505.00 +/- 20.00 µm	ADE, 100%
	14.0	Handle Doping Type	N	Wafer Vendor
	15.0	Handle Dopant	Any	Wafer Vendor
	16.0	Handle Resistivity	0.001 ~ 0.005 Ohmcm	Wafer Vendor
	17.0	Handle Carbon Concentration	<5.0 E16 atoms / cm3	Wafer vendor - guranteed by process.
	18.0	Backside Finish	Polished with lasermark and no oxide.	Wafer Vendor
DeviceSilicon	19.0	Device Growth Method	FZ	Wafer Vendor - Topsil only
	20.0	Device Orientation	{100} +/- 1 degree	Wafer Vendor
	21.0	Nominal Thickness	170.00 +/- 2.00 µm	FTIR, 100% 9-Pt (note3)
	22.0	Distance to device silicon edge from wafer edge	< 2 mm	Guaranteed by Process
	23.0	Device Doping Type	P	Wafer Vendor
	24.0	Device Dopant	Boron	Wafer Vendor
	25.0	Device Resistivity	>1000 Ohm-cm	Wafer Vendor
	26.0	Oxygen Concentration	<2.6 E16 atoms / cm3	Wafer vendor - guranteed by FZ process.
	27.0	Carbon Concentration	<2.0 E16 atoms / cm3	Wafer vendor - guranteed by process.
	28.0	Buried Layer Implant	none	implant vendor
	29.0	Voids	0	Bright Light, 100% (note 2)
	30.0	Scratches	Total length 25mm	Bright Light, 100% (note 2)
	31.0	Haze	none	Bright Light, 100% (note 2)

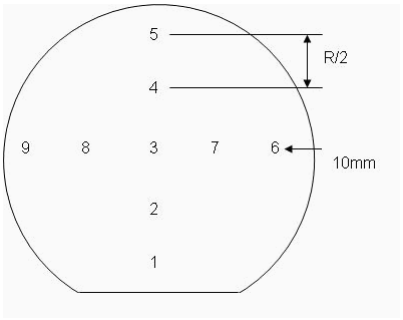
Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information